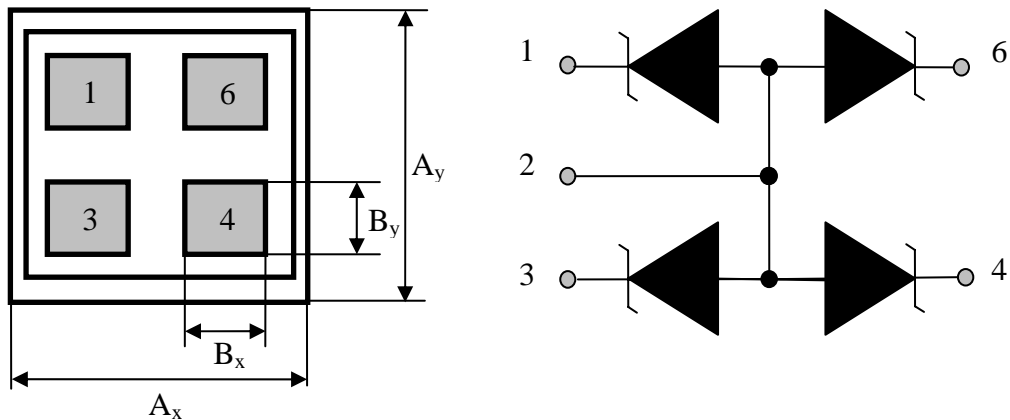


## KS-5,0V4L1

Chip low capacitance 4- fold ESD protection diode.



**Mechanical date:**  $A_x=A_y=340\mu\text{m}$ .      **Schematic and pinning diagram.**

$B_x=B_y=70\mu\text{m}$

**Chip thickness:**  $230\pm 20\mu\text{m}$

**Scribe Line width** -  $60\mu\text{m}$ .

**Top Metal:** Al - for wire bonding.

**Back side - Anode:** Ti-Ni-Ag for soldering.

### Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	$V_{RWM}$	-	5,0	V
Peak Pulse Power	$P_{pp}$	$t_p=8/20\mu\text{s}$	25*	W
Peak Pulse Current	$I_{pp}$	$t_p=8/20\mu\text{s}$	2,0*	A
Electrostatic Discharge	$V_{ESD}$	IEC 61000-4-2, level 4.	>8 (Contact); >15(Air).	kV
Max.junction temperature	$T_j$	-	+150	°C

### Characteristics ( $T_j=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_R$	Reverse leakage current	$V=3,0\text{V}$	-	-	0,9	$\mu\text{A}$
$V_{BR}$	Breakdown voltage	$I_R=1\mu\text{A}$	6,15	-	7,15	V
$C_J$	Diode capacitance	$F=1\text{MHz}$ , $V_R=3,0\text{V}$	-	-	9,5	pF
$R_{diff}$	Differential resistance	$I_R=15\text{A}$ , $t_p=2,5\mu\text{s}$	-	-	1,1*	Ohm

\*- For Device testing